NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE3407 uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -30V, I_{D} = -4.6A$

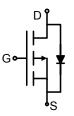
 $R_{DS(ON)} < 95m\Omega @ V_{GS} = -4.5V$

 $R_{DS(ON)}$ < 65m Ω @ V_{GS} =-10V

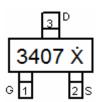
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3407 X	NCE3407	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	-4.6	Α
Drain Current-Pulsed (Note 1)	I _{DM}	-20	Α
Maximum Power Dissipation	P _D	1.4	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	90	°C/W

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V,V _{GS} =0V	-	-	-1	μA



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Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)		•				
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA	-1.1	-1.5	-2.2	V
Drain Course On Ctata Desistance		V _{GS} =-10V, I _D =-4.6A	-	48	65	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4A	-	60	95	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-4.6A	-	10	-	S
Dynamic Characteristics (Note4)		•				
Input Capacitance	C _{lss}	\/ 45\/\/ 0\/	-	650	-	PF
Output Capacitance	C _{oss}	V _{DS} =-15V,V _{GS} =0V, — F=1.0MHz —		105	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UMHZ	-	65	-	PF
Switching Characteristics (Note 4)		•				
Turn-on Delay Time	t _{d(on)}		-	8.5	-	nS
Turn-on Rise Time	t _r	V _{DD} =-15V,R _L =3.6Ω	-	4.5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10V, R_{GEN} =3 Ω	-	26	-	nS
Turn-Off Fall Time	t _f		-	12.5	-	nS
Total Gate Charge	Qg		-	12.5	-	nC
Gate-Source Charge	Q _{gs} V _{DS} =-15V,I _D =-4.6A,V _{GS} =-10V		-	2.8	-	nC
Gate-Drain Charge	Q_{gd}		-	2.7	-	nC
Drain-Source Diode Characteristics	•					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-4.6A	-	-	-1.2	V

Notes:

- Repetitive Rating: Pulse width limited by maximum junction temperature.
 Surface Mounted on FR4 Board, t ≤ 10 sec.
 Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

- 4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

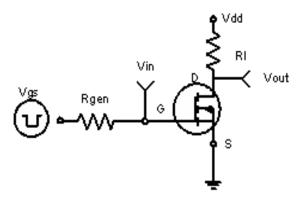


Figure 1:Switching Test Circuit

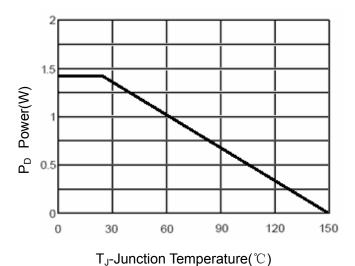


Figure 3 Power Dissipation

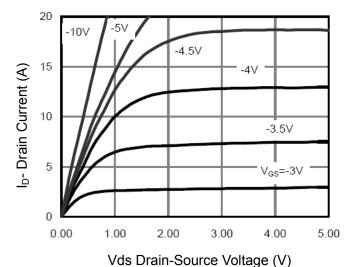


Figure 5 Output Characteristics

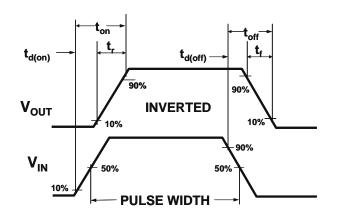


Figure 2:Switching Waveforms

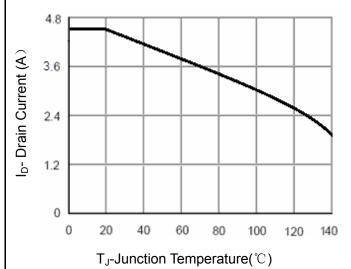


Figure 4 Drain Current

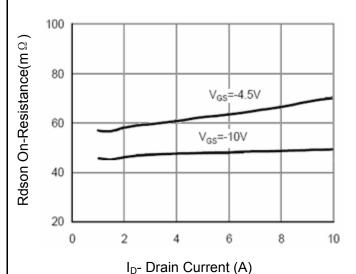
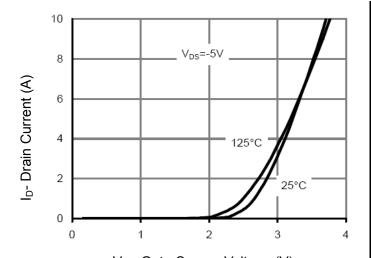
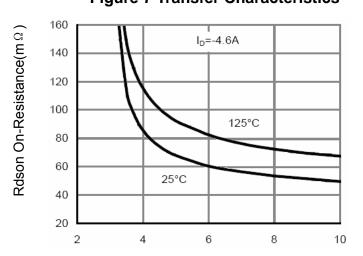


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V) Figure 9 Rdson vs Vgs

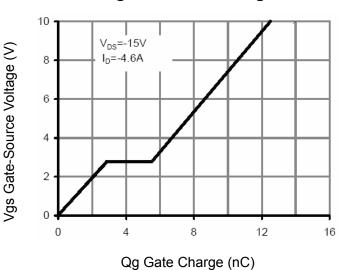


Figure 11 Gate Charge

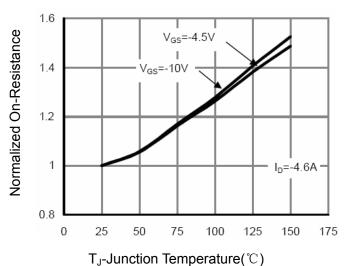
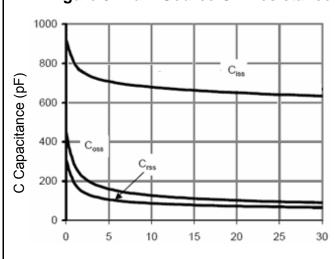


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

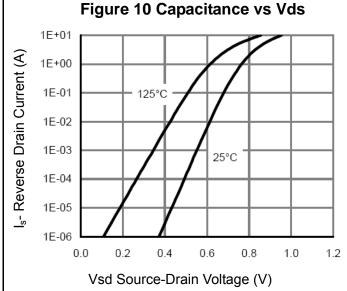
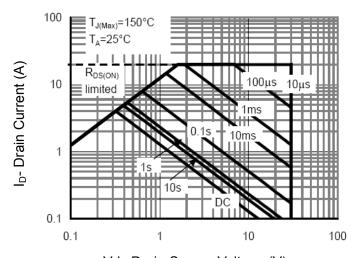


Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

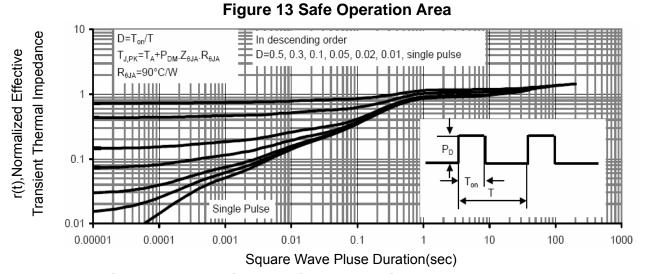
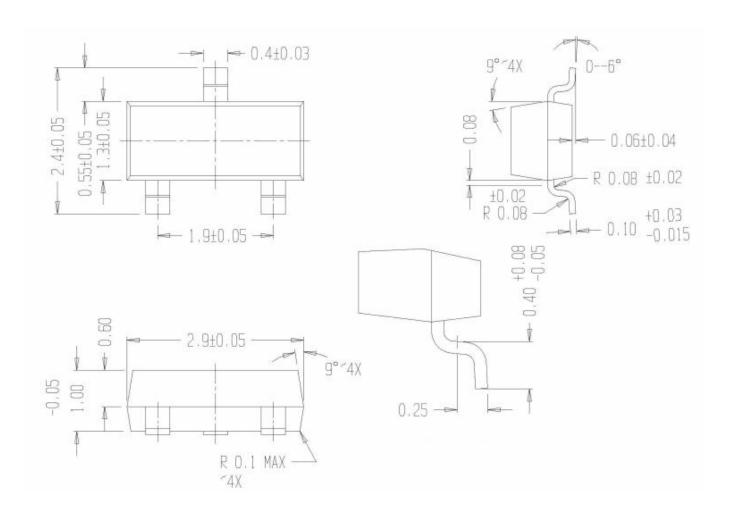
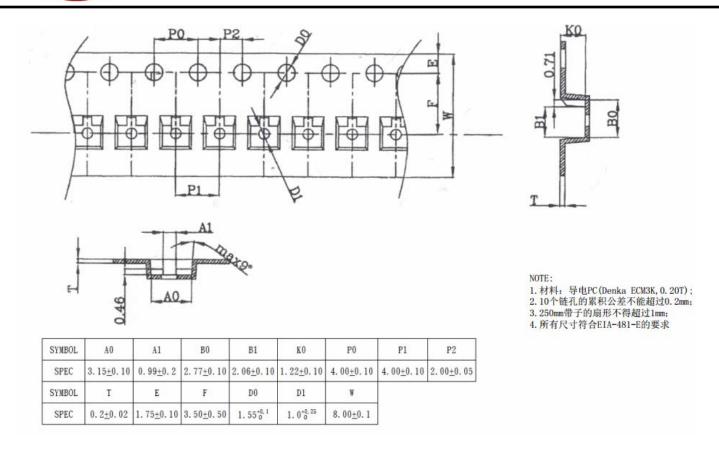


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information





Carrier Tape

PKG TYPE	Lead count	Tape Width	Reel Diameter	QTY/Reel	QTY/Outer Box	G.W.(kg)
SOT-23	3	8mm	T	3000	180000	6.5

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